### VS-25TTS08FP-M3, VS-25TTS12FP-M3

Vishay Semiconductors

RoHS COMPLIANT

## Thyristor High Voltage, Phase Control SCR, 25 A



| PRIMARY CHARACTERISTICS |                   |  |  |  |
|-------------------------|-------------------|--|--|--|
| I <sub>T(AV)</sub>      | 16 A              |  |  |  |
| $V_{DRM}/V_{RRM}$       | 800 V, 1200 V     |  |  |  |
| $V_{TM}$                | 1.25 V            |  |  |  |
| I <sub>GT</sub>         | 45 mA             |  |  |  |
| $T_J$                   | -40 °C to 125 °C  |  |  |  |
| Package                 | 3L TO-220 FullPAK |  |  |  |
| Circuit configuration   | Single SCR        |  |  |  |

#### **FEATURES**

- · Designed and qualified for industrial level
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL pending
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## HALOGEN **FREE**

#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

### **DESCRIPTION**

The VS-25TTS...FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS   |                     |                    |       |  |  |  |
|--|---------------------|--------------------|-------|--|--|--|
| APPLICATIONS   | SINGLE-PHASE BRIDGE | THREE-PHASE BRIDGE | UNITS |  |  |  |
| Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W | 18                  | 22                 | А     |  |  |  |

| MAJOR RATINGS AND CHARACTERISTICS  |                              |             |       |  |  |
|------------------------------------|------------------------------|-------------|-------|--|--|
| PARAMETER                          | TEST CONDITIONS              | VALUES      | UNITS |  |  |
| I <sub>T(AV)</sub>                 | Sinusoidal waveform          | 16          | Δ.    |  |  |
| I <sub>RMS</sub>                   |                              | 25          | Α     |  |  |
| V <sub>RRM</sub> /V <sub>DRM</sub> |                              | 800, 1200   | V     |  |  |
| I <sub>TSM</sub>                   |                              | 350         | A     |  |  |
| V <sub>T</sub>                     | 16 A, T <sub>J</sub> = 25 °C | 1.25        | V     |  |  |
| dV/dt                              |                              | 500         | V/µs  |  |  |
| dI/dt                              |                              | 150         | A/µs  |  |  |
| TJ                                 |                              | -40 to +125 | °C    |  |  |

| VOLTAGE RATINGS |   |  |   |  |  |  |
|-----------------|---|--|---|--|--|--|
| PART NUMBER     | V <sub>RRM</sub> , MAXIMUM PEAK<br>REVERSE VOLTAGE<br>V | V <sub>DRM</sub> , MAXIMUM PEAK<br>DIRECT VOLTAGE<br>V | I <sub>RRM</sub> /I <sub>DRM</sub><br>AT 125 °C<br>mA |  |  |  |
| VS-25TTS08FP-M3 | 800   | 800  | 10  |  |  |  |
| VS-25TTS12FP-M3 | 1200  | 1200   | 1.0   |  |  |  |



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| ABSOLUTE MAXIMUM RATINGS                   |                                  |  |           |                  |
|--|----------------------------------|--|-----------|------------------|
| PARAMETER                                  | SYMBOL                           | TEST CONDITIONS  | VALUES    | UNITS            |
| PANAMEIEN                                  |                                  | TEST CONDITIONS  | TYP. MAX. |                  |
| Maximum average on-state current           | I <sub>T(AV)</sub>               | T <sub>C</sub> = 51 °C, 180° conduction half sine wave                       | 16        |                  |
| Maximum RMS on-state current               | I <sub>RMS</sub>                 |  | 25        | Α                |
| Maximum peak, one-cycle,                   |                                  | 10 ms sine pulse, rated V <sub>RRM</sub> applied                             | 300       |                  |
| non-repetitive surge current               | I <sub>TSM</sub>                 | 10 ms sine pulse, no voltage reapplied                                       | 350       |                  |
| Marriage participa                         | 124                              | 10 ms sine pulse, rated V <sub>RRM</sub> applied                             | 450       | A <sup>2</sup> s |
| Maximum I <sup>2</sup> t for fusing        | l <sup>2</sup> t                 | 10 ms sine pulse, no voltage reapplied                                       | 630       | A-S              |
| Maximum I <sup>2</sup> √t for fusing       | I <sup>2</sup> √t                | t = 0.1ms to 10 ms, no voltage reapplied                                     | 6300      | A²√s             |
| Maximum on-state voltage drop              | $V_{TM}$                         | 16 A, T <sub>J</sub> = 25 °C   | 1.25      | V                |
| On-state slope resistance                  | r <sub>t</sub>                   | T <sub>.I</sub> = 125 °C   | 12.0      | mΩ               |
| Threshold voltage                          | V <sub>T(TO)</sub>               | 1j=125 C   | 1.0       | V                |
| Maximum reverse and direct leakage current | I <sub>RM</sub> /I <sub>DM</sub> | $T_J = 25 ^{\circ}\text{C}$ $V_R = \text{Rated } V_{RRM}/V_{DRM}$            | 0.5       |                  |
| Maximum reverse and direct leakage current | 'RM' 'DM                         | T <sub>J</sub> = 125 °C  | 10        |                  |
| Holding current                            | I <sub>H</sub>                   | Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C       |           | mA               |
| Maximum latching current                   | Ι <sub>L</sub>                   | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 2                 |           |                  |
| Maximum rate of rise of off-state voltage  | dV/dt                            | $T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ |           | V/µs             |
| Maximum rate of rise of turned-on current  | dI/dt                            |  | 150       | A/µs             |

| TRIGGERING                                  |                    |  |        |       |
|---|--------------------|--|--------|-------|
| PARAMETER                                   | SYMBOL             | TEST CONDITIONS  | VALUES | UNITS |
| Maximum peak gate power                     | P <sub>GM</sub>    |  | 8.0    | w     |
| Maximum average gate power                  | P <sub>G(AV)</sub> |  | 2.0    | ] vv  |
| Maximum peak positive gate current          | + I <sub>GM</sub>  |  | 1.5    | Α     |
| Maximum peak negative gate voltage          | - V <sub>GM</sub>  |  | 10     | V     |
| Maximum required DC gate current to trigger | l <sub>GT</sub>    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C | 60     | mA    |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 45     |       |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 20     |       |
| Maximum vacuired DC cata                    |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C | 2.5    |       |
| Maximum required DC gate voltage to trigger | V <sub>GT</sub>    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 2.0    | 1 ,,  |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 1.0    | V     |
| Maximum DC gate voltage not to trigger      | $V_{GD}$           | T 405 00 W But d at a  | 0.25   |       |
| Maximum DC gate current not to trigger      | I <sub>GD</sub>    | T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value      |        | mA    |

| SWITCHING                     |                 |                          |        |       |
|-------------------------------|-----------------|--------------------------|--------|-------|
| PARAMETER                     | SYMBOL          | TEST CONDITIONS          | VALUES | UNITS |
| Typical turn-on time          | t <sub>gt</sub> | T <sub>J</sub> = 25 °C   | 0.9    |       |
| Typical reverse recovery time | t <sub>rr</sub> | T <sub>.1</sub> = 125 °C | 4      | μs    |
| Typical turn-off time         | t <sub>q</sub>  | 1j = 125 C               | 110    |       |



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| THERMAL AND MECHANICAL SPECIFICATIONS           |         |                              |                                       |            |            |
|---|---------|------------------------------|---------------------------------------|------------|------------|
| PARAMETER                                       |         | SYMBOL                       | TEST CONDITIONS                       | VALUES     | UNITS      |
| Maximum junction and storage temperature range  |         | $T_J$ , $T_{Stg}$            |                                       | -40 to 125 | °C         |
| Maximum thermal resistance, junction to case    |         | $R_{\text{thJC}}$            | DC operation                          | 2.5        |            |
| Maximum thermal resistance, junction to ambient |         | R <sub>thJA</sub>            |                                       | 62         | °C/W       |
| Typical thermal resistance, case to heatsink    |         | R <sub>thCS</sub>            | Mounting surface, smooth, and greased | 0.5        |            |
| Approximate weight                              |         |                              |                                       | 2          | g          |
| Approximate weight                              |         |                              |                                       | 0.07       | OZ.        |
| Mounting torque                                 | minimum |                              |                                       | 6 (5)      | kgf · cm   |
| Woulding torque                                 | maximum |                              |                                       | 12 (10)    | (lbf ⋅ in) |
| Madina davisa                                   |         | Case style 3L TO-220 FullPAK | 25TTS0                                | 8FP        |            |
| Marking device                                  |         |                              |                                       | 25TTS1:    | 2FP        |

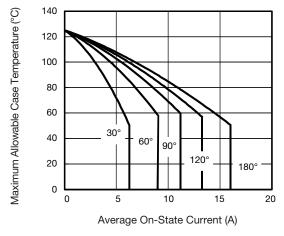


Fig. 1 - Current Rating Characteristics

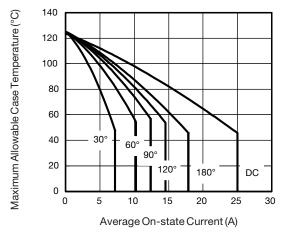


Fig. 2 - Current Rating Characteristics

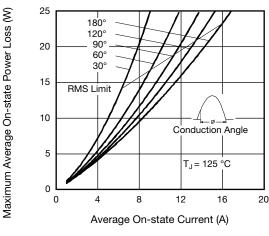


Fig. 3 - On-State Power Loss Characteristics

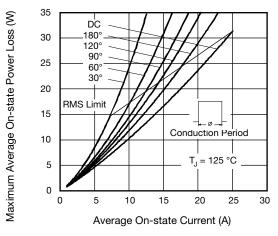


Fig. 4 - On-State Power Loss Characteristics

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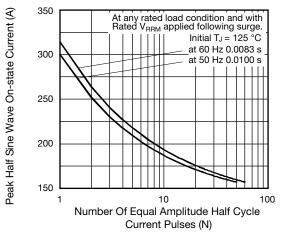


Fig. 5 - Maximum Non-Repetitive Surge Current

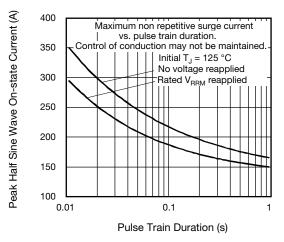


Fig. 6 - Maximum Non-Repetitive Surge Current

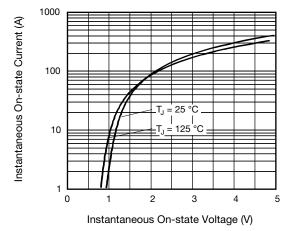


Fig. 7 - On-State Voltage Drop Characteristics

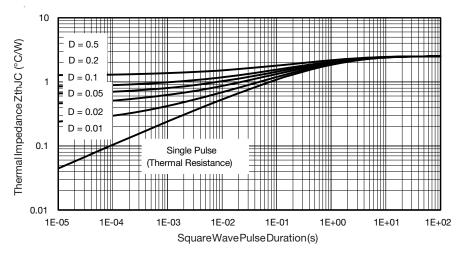
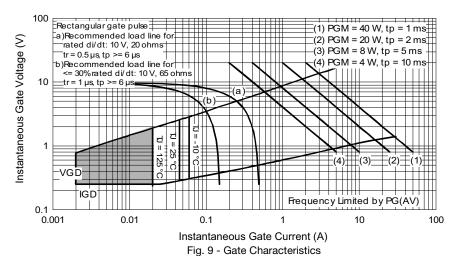


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

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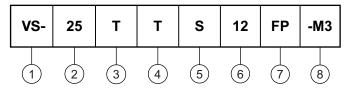
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### **ORDERING INFORMATION TABLE**

#### Device code



- Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- 3 Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

Standard recovery rectifier

7 - FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) |                  |                        |                          |  |  |
|--------------------------------|------------------|------------------------|--------------------------|--|--|
| PREFERRED P/N                  | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION    |  |  |
| VS-25TTS08FP-M3                | 50               | 1000                   | Antistatic plastic tubes |  |  |
| VS-25TTS12FP-M3                | 50               | 1000                   | Antistatic plastic tubes |  |  |

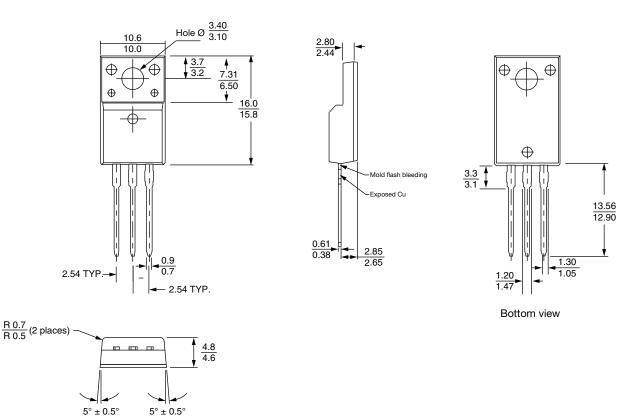
| LINKS TO RELATED DOCUMENTS                 |                          |  |  |  |  |
|--|--------------------------|--|--|--|--|
| Dimensions <u>www.vishay.com/doc?96155</u> |                          |  |  |  |  |
| Part marking information                   | www.vishay.com/doc?95456 |  |  |  |  |



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### **3L TO-220 FullPAK**

### **DIMENSIONS** in millimeters



#### **Notes**

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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